TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA2374FK

Low-Voltage Octal D-Type Flip-Flop with 3.6 V Tolerant Inputs and Outputs

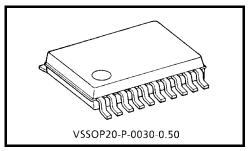
The TC7MA2374FK is a high performance CMOS octal D-type flip-flop. Designed for use in $1.8~\rm{V},\,2.5~\rm{V}$ or $3.3~\rm{V}$ systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\ V\!.$

This 8 bit D-type flip-flop is controlled by a clock input (CK) and output enable input (\overline{OE}) . When the \overline{OE} input is high, the eight outputs are in a high impedance state.

The $26~\Omega$ series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

Features

- 26Ω series resistors on outputs.
- Low voltage operation: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation: $t_{pd} = 5.1 \text{ ns (max)} (V_{CC} = 3.0 \sim 3.6 \text{ V})$

 $t_{pd} = 6.2 \text{ ns (max) (V}_{CC} = 2.3 \sim 2.7 \text{ V})$

 $t_{pd} = 9.8 \text{ ns (max) (V}_{CC} = 1.8 \text{ V})$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $I_{OH}/I_{OL} = \pm 8 \text{ mA (min)} (V_{CC} = 2.3 \text{ V})$

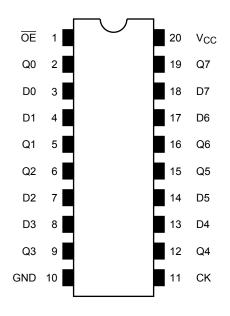
 $I_{OH}/I_{OL} = \pm 4 \text{ mA (min) (V}_{CC} = 1.8 \text{ V)}$

- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200 \text{ V}$

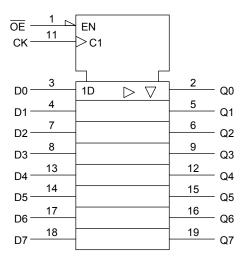
Human body model $\geq \pm 2000 \text{ V}$

- Package: VSSOP (US)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)
 - *: To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Pin Assignment (top view)



IEC Logic Level



Truth Table

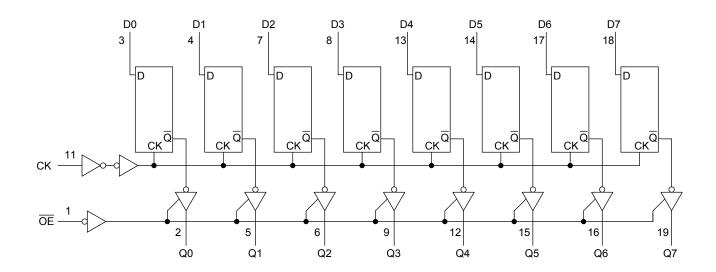
	Inputs	Outputs	
ŌĒ	CK	D	Outputs
Н	Х	X	Z
L		Х	Qn
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Q_n: No change

System Diagram



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Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage	V _{IN}	-0.5~4.6	V
DC output voltage	V _{OUT}	-0.5~4.6 (Note 2)	V
DC output voltage	VOUI	-0.5~V _{CC} + 0.5 (Note 3)	V
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	lout	±50	mA
Power dissipation	P _D	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Off-state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: Vout < GND, Vout > Vcc

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	1.8~3.6		
Supply Voltage	VCC	1.2~3.6 (Note 2)	V	
Input voltage	V _{IN}	-0.3~3.6	>	
Output voltage	Vour	0~3.6 (Note 3)	V	
Output voltage	V _{OUT}	0~V _{CC} (Note 4)	V	
		±12 (Note 5)		
Output current	I _{OH} /I _{OL}	±8 (Note 6)	mA	
		±4 (Note 7)		
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	0~10 (Note 8)	ns/V	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

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Note 2: Data retention only

Note 3: Off-state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 \text{ V}$

Note 8: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$



Electrical Characteristics

DC Characteristics (Ta = $-40~85^{\circ}$ C, 2.7 V < V_{CC} \leq 3.6 V)

Characteri	stics	Symbol	Test	Condition	V _{CC} (V)	Min	Max	Unit
	High level	V _{IH}		_	2.7~3.6	2.0		
Input voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	V
				I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	_	
	High level	VoH	V _{IN} = V _{IH} or V _{II}	I _{OH} = -6 mA	2.7	2.2	_	
				$I_{OH} = -8 \text{ mA}$	3.0	2.4	_	
Output voltage				I _{OH} = -12 mA	3.0	2.2	_	V
		V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	2.7~3.6	_	0.2	
l and land	Low level			I _{OL} = 6 mA	2.7	_	0.4	
	Low level			$I_{OL} = 8 \text{ mA}$	3.0	_	0.55	
				$I_{OL} = 12 \text{ mA}$	3.0	_	0.8	
Input leakage curre	nt	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μΑ
3-state output off-state current		I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6 \text{ V}$		2.7~3.6	_	±10.0	μΑ
Power off leakage of	urrent	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
	laa	V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0		
Quiescent supply co	Quiescent supply current	Icc	V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7~3.6	_	±20.0	μΑ
		Δlcc	$V_{IH} = V_{CC} - 0.6 V$ (per	input)	2.7~3.6	_	750	

DC Characteristics (Ta = $-40~85^{\circ}$ C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteristics		Symbol	nbol Test Condition			Min	Max	Unit		
Silarasto	1101100	Cymbol	100	rest condition			Max	Onic		
Input voltage	High level	V _{IH}		_	2.3~2.7	1.6	_	V		
Input voltage	Low level	V _{IL}		_	2.3~2.7	_	0.7	V		
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_			
	High level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -4 mA	2.3	2.0	_			
			V _{OL} V _{IN} = V _{IH} or V _{IL}			I _{OH} = -6 mA	2.3	1.8	_	
Output voltage				$I_{OH} = -8 \text{ mA}$	2.3	1.7	_	V		
				V_{OL} $V_{IN} = V_{IH}$ or V_{IL}	V_{OL} $V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 100 \mu\text{A}$ $I_{OL} = 6 \text{mA}$	$I_{OL} = 100 \mu A$	2.3~2.7	_	0.2	
	Low level	V_{OL}				I _{OL} = 6 mA	2.3	_	0.4	
				I _{OL} = 8 mA	2.3	_	0.6			
Input leakage curre	ent	I _{IN}	V _{IN} = 0~3.6 V	·	2.3~2.7	_	±5.0	μΑ		
3-state output off-state current		1	$V_{IN} = V_{IH}$ or V_{IL}		2.3~2.7		. 40.0	^		
		loz	V _{OUT} = 0~3.6 V		2.3~2.1		±10.0	μА		
Power off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА		
		V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0	^			
Quiescent supply current		Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3~2.7	_	±20.0	μА		

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DC Characteristics (Ta = $-40\sim85^{\circ}$ C, 1.8 V \leq V_{CC} < 2.3 V)

Characteris	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	High level	V _{IH}		_	1.8~2.3	0.7 × V _{CC}	_	V
input voltage	Low level	V _{IL}		_	1.8~2.3	_	0.2 × V _{CC}	V
	High level	VoH	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage				$I_{OH} = -4 \text{ mA}$	1.8	1.4	_	V
	Low level	V/a-:	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	1.8	_	0.2	
	Low level	V _{OL}		$I_{OL} = 4 \text{ mA}$	1.8	_	0.3	
Input leakage currer	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8	_	±5.0	μΑ
3-state output off-sta	s-state output off-state current I_{OZ} $V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \sim 3.6 \text{ V}$			1.8	_	±10.0	μА	
Power off leakage c	urrent	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА
O de constitución de la constitu		loo	V _{IN} = V _{CC} or GND		1.8	_	20.0	μА
Quiescent supply cu	III CIII	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8	_	±20.0	μΑ

AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500~\Omega$)

Characteristics	Symbol	Symbol Test Condition		Min	Max	Unit
Characteristics	Symbol Test condition		V _{CC} (V)			Orme
			1.8	100	_	
Maximum clock frequency	f _{max}	Figure 1, Figure 2	2.5 ± 0.2	200	_	MHz
			3.3 ± 0.3	250	_	
	4		1.8	1.5	9.8	
Propagation delay time (CK-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	8.0	6.2	ns
	tpHL		3.3 ± 0.3	0.6	5.1	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	0.8	6.5	ns
	t _{pZH}		3.3 ± 0.3	0.6	5.0	
		Figure 1, Figure 3	1.8	1.5	7.7	ns
3-state output disable time	t _{pLZ}		2.5 ± 0.2	0.8	4.3	
	t _{pHZ}		3.3 ± 0.3	0.6	3.9	
	t _{w (H)}	Figure 1, Figure 2	1.8	4.0	_	ns
Minimum pulse width (CK)			2.5 ± 0.2	1.5	_	
			3.3 ± 0.3	1.5	_	
			1.8	2.5	_	
Minimum set-up time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
			1.8	_	0.5	
Output to output skew	tosLH	(Note)	2.5 ± 0.2	_	0.5	ns
	tosHL		3.3 ± 0.3	_	0.5	

For $C_L = 50\ pF$, add approximately 300 ps to the AC maximum specification.

Note: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f$ = 2.0 ns, C_L = 30 pF)

Characteristics	Symbol	Test Condition	V	/cc (V)	Тур.	Unit
		V _{IH} = 1.8 V, V _{IL} = 0 V (No	te)	1.8	0.15	
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 2.5 V, V _{IL} = 0 V (No	te)	2.5	0.25	V
		V _{IH} = 3.3 V, V _{IL} = 0 V (No	te)	3.3	0.35	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	1.8	-0.15	V
Quiet output minimum dynamic V_{OL}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	2.5	-0.25	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	3.3	-0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	1.8	1.55	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te)	3.3	2.65	

Note: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

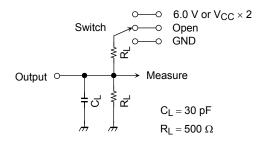
Characteristics	Symbol	Test Condition		Tun	Unit
Characteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	UIIIL
Input capacitance	C _{IN}	_	1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Not	e) 1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		Switch	
t _{pLH} , t _{pHL}		Open		
t _{pLZ} , t _{pZL}	$V_{CC} \times 2$	$@V_{CC} = 3.3 \pm 0.3 \text{ V} \\ @V_{CC} = 2.5 \pm 0.2 \text{ V} \\ @V_{CC} = 1.8 \text{ V}$		
t _{pHZ} , t _{pZH}		GND		

Figure 1

AC Waveform

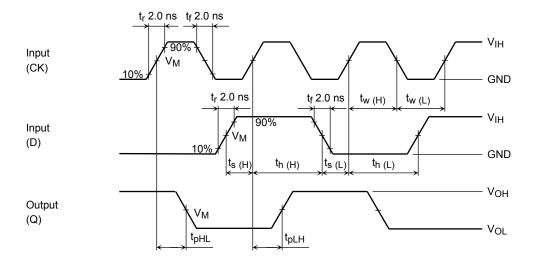


Figure 2 t_{pLH} , t_{pHL} , t_w , t_s , t_h

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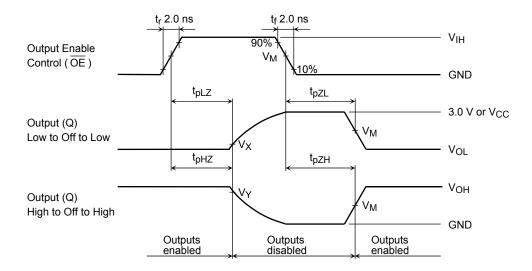
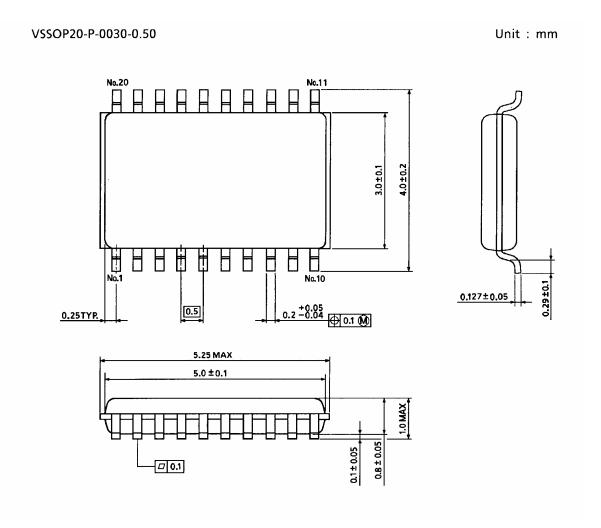


Figure 3 $t_{\text{pLZ}},\,t_{\text{pHZ}},\,t_{\text{pZL}},\,t_{\text{pZH}}$

Symbol	Vcc						
Symbol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V				
V _{IH}	2.7 V	V _{CC}	V _{CC}				
V_{M}	1.5 V	V _{CC} /2	V _{CC} /2				
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V				
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V				

9 2007-10-19

Package Dimensions



Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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